



FORM PTO-1449 (SUBSTITUTE)

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEINFORMATION DISCLOSURE
STATEMENT BY APPLICANT
(37 CFR 1.98(b))

Attorney Docket No.:

P2001,0158

Applic. No.

10/657,928

Applicant

Wolfgang Gustin et al.

Filing Date

September 10, 2003

Group Art Unit

U.S. PATENT DOCUMENTS

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A						
	B						
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		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
	J						
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	M						
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

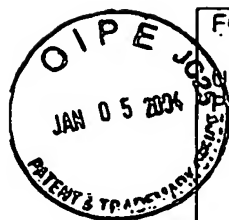
7BKS	O	L. Nesbit et al.: "A 0.6 μm^2 256Mb Trench DRAM Cell With Self-Aligned BuriEd STrap (BEST)", <i>IEDM 1993</i> , pp. 627-630
7BKS	P	G. Bronner et al.: "A Fully planarized 0.25 μm CMOS Technology for 256Mbit DRAM and Beyond", <i>1995 Symposium on VLSI Technology Digest of technical Papers, Kyoto, Japan</i> , pp. 15-16

EXAMINER

DATE CONSIDERED

7/8/04

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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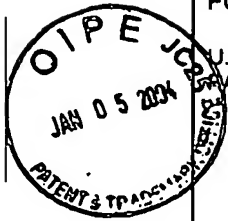
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	M						
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

<i>SKS</i>	O	Stanley Wolf: "Silicon Processing For The VLSI Era – Volume 2: Process Integration", <i>Lattice Press, Sunset Beach, California, cover page only</i>
<i>SKS</i>	P	D. Widmann et al.: "Technologie hochintegrierter Schaltungen", <i>Springer Verlag, Heidelberg, Germany, 2nd ed., cover page only</i>
EXAMINER	DATE CONSIDERED	
<i>SKS</i>	7/8/04	

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75/LS	O	U. Gruening et al.: A Novel Trench DRAM Cell with a <u>VERT</u> ical Access Transistor and <u>Buri</u> Ed Strap (VERI BEST) for 4Gb/16Gb", IEEE, 1999, 4 pp
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EXAMINER INITIALS	PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
BKS	A	5,744,386	4/28/98	Kenney		
BKS	B	5,827,765	10/27/98	Stengl et al.		
BKS	C	5,670,805	9/23/97	Hammerl et al.		
BKS	D	5,360,758	11/1/94	Bronner et al.		
BKS	E	6,509,599 B1	1/21/03	Wurster et al.		
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DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO		
BKS	J	196 20 625 C1	10/23/97	Germany			
BKS	K	100 45 694 A1	4/4/02	Germany			
BKS	L	0 971 414 A1	1/12/00	Europe			
BKS	M	00/35006	6/15/00	WIPO			
	N						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)	
	Gruening, U. et al.: "A Novel DRAM Cell with a VERTlcal Access Transistor and BuriEd STRap (VERI BEST) for 4Gb/16Gb", IEEE, 1999, 4 pages
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